

Thus, in 1D, utilizing the Einstein relationship, the electric field can be written as

$$\vec{E} = \frac{kT}{q} \frac{1}{p_o} \frac{dp_o}{dx} \quad (3.92)$$

Rewriting equation (3.85) and substituting equation (3.92) yields

$$V_{bi} = \int_{-x_N}^{x_P} \vec{E} dx = \int_{-x_N}^{x_P} \frac{kT}{q} \frac{1}{p_o} \frac{dp_o}{dx} dx = \frac{kT}{q} \int_{p_o(-x_N)}^{p_o(x_P)} \frac{dp_o}{p_o} = \frac{kT}{q} \ln \left[\frac{p_o(x_P)}{p_o(-x_N)} \right] \quad (3.93)$$

Since we have assumed nondegeneracy, $p_o(x_P) = N_A$ and $p_o(-x_N) = n_i^2/N_D$. Therefore,

$$V_{bi} = \frac{kT}{q} \ln \left[\frac{N_D N_A}{n_i^2} \right]. \quad (3.94)$$

Figure 3.14 shows the equilibrium energy band diagram, electric field, and charge density for a simple abrupt pn -junction silicon diode in the vicinity of the depletion region. The conduction bandedge is given by $E_C(x) = E_0 - q\phi(x) - \chi$, the valence bandedge

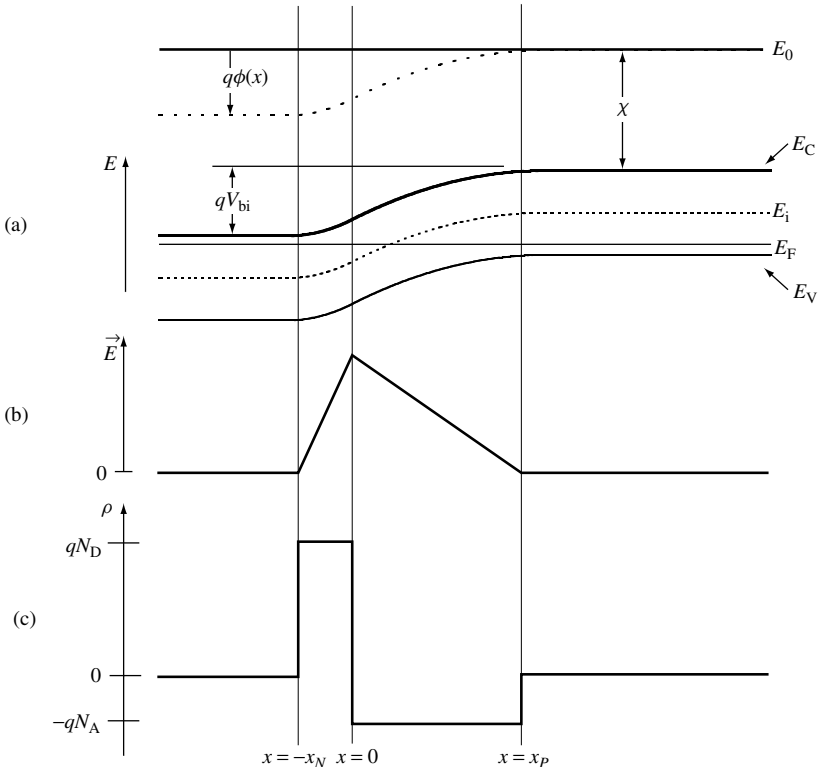


Figure 3.14 Equilibrium conditions in a solar cell: (a) energy bands; (b) electric field; and (c) charge density